

# 1N4150

## FEATURES :

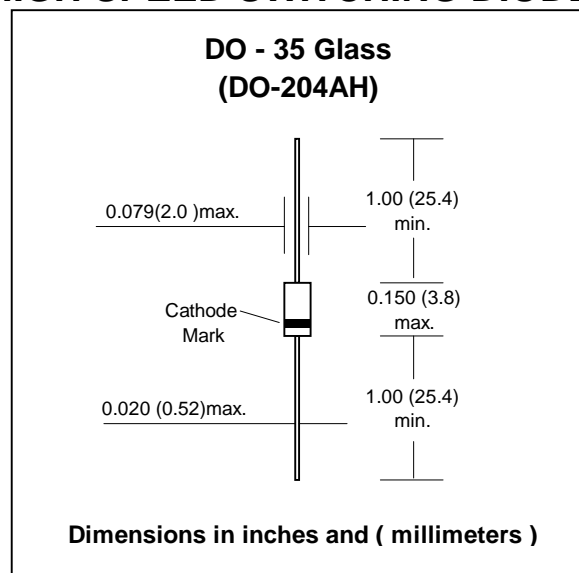
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 50 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 600 mA
- **Pb / RoHS Free**

## MECHANICAL DATA :

**Case:** DO-35 Glass Case

**Weight:** approx. 0.13g

## HIGH SPEED SWITCHING DIODE



## Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

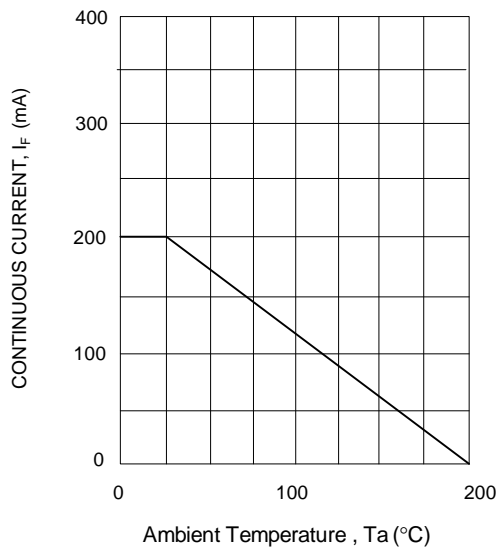
Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	75	V
Maximum Continuous Reverse Voltage	$V_{RM}$	50	V
Maximum Continuous Forward Current	$I_F$	200	mA
Maximum Power Dissipation	$P_D$	500	mW
Maximum Repetitive Peak Forward Current	$I_{FRM}$	600	mA
Maximum Surge Forward Current at $t = 1s$ , $T_j = 25^\circ C$	$I_{FSM}$	0.5	A
Maximum Junction Temperature	$T_J$	200	$^\circ C$
Storage Temperature Range	$T_S$	-65 to + 200	$^\circ C$

## Electrical Characteristics ( $T_J = 25^\circ C$ unless otherwise noted)

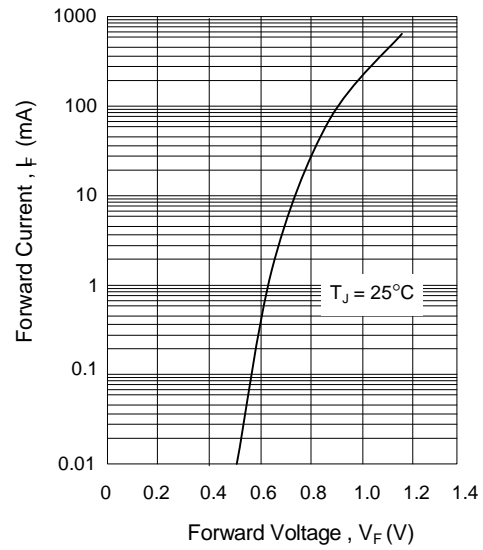
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Current	$I_R$	$V_R = 50 V$	-	-	0.1	$\mu A$
		$V_R = 50 V$ , $T_j = 150^\circ C$	-	-	100	$\mu A$
Forward Voltage	$V_F$	$I_F = 100 mA$	-	-	0.92	V
		$I_F = 200 mA$	-	-	1.0	V
Diode Capacitance	$C_d$	$f = 1MHz$ ; $V_R = 0$	-	-	2.5	pF
Reverse Recovery Time	$T_{rr}$	$I_F = 10 mA$ to 200 mA to $I_R = 10 mA$ to 200 mA; $R_L = 100 \Omega$ ; measured at $I_R = 0.1 \times I_F$	-	-	4	ns

### RATING AND CHARACTERISTIC CURVES ( 1N4150 )

**FIG. 1 MAXIMUM FORWARD CURRENT VERSUS AMBIENT TEMPERATURE**



**FIG. 2 TYPICAL FORWARD VOLTAGE**



**FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE**

